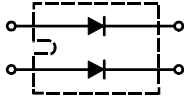
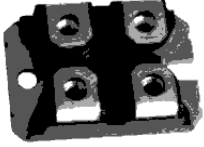
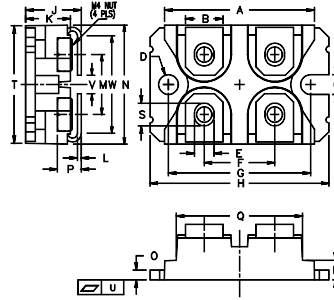


# SUR2x30-08, SUR2x30-10

## Ultra Fast Recovery Epitaxial Diodes



Dimensions SOT-227(ISOTOP)



Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	31.50	31.88	1.240	1.255
B	7.80	8.20	0.307	0.323
C	4.09	4.29	0.161	0.169
D	4.09	4.29	0.161	0.169
E	4.09	4.29	0.161	0.169
F	14.91	15.11	0.587	0.595
G	30.12	30.30	1.186	1.193
H	37.80	38.20	1.489	1.505
J	11.68	12.22	0.460	0.481
K	8.92	9.60	0.351	0.378
L	0.76	0.84	0.030	0.033
M	12.60	12.85	0.496	0.506
N	25.15	25.42	0.990	1.001
O	1.98	2.13	0.078	0.084
P	4.95	5.97	0.195	0.235
Q	26.54	26.90	1.045	1.059
R	3.94	4.42	0.155	0.174
S	4.72	4.85	0.186	0.191
T	24.59	25.07	0.968	0.987
U	-0.05	0.1	-0.002	0.004
V	3.30	4.57	0.130	0.180
W	0.780	0.830	0.031	0.033

	$V_{RSM}$	$V_{RRM}$
	V	V
<b>SUR2x30-08</b>	800	800
<b>SUR2x30-10</b>	1000	1000

Symbol	Test Conditions	Maximum Ratings	Unit
$I_{FRMS}$	$T_{VJ}=T_{VJM}$	70	A
$I_{FAVM}$	$T_C=50^{\circ}C$ ; rectangular, $d=0.5$	30	
$I_{FRM}$	$t_p < 10\mu s$ ; rep. rating, pulse width limited by $T_{VJM}$	375	
$I_{FSM}$	$T_{VJ}=45^{\circ}C$	$t=10ms$ (50Hz), sine $t=8.3ms$ (60Hz), sine	A
	$T_{VJ}=150^{\circ}C$	$t=10ms$ (50Hz), sine $t=8.3ms$ (60Hz), sine	
$I^2t$	$T_{VJ}=45^{\circ}C$	$t=10ms$ (50Hz), sine $t=8.3ms$ (60Hz), sine	$A^2s$
	$T_{VJ}=150^{\circ}C$	$t=10ms$ (50Hz), sine $t=8.3ms$ (60Hz), sine	
$T_{VJ}$		-40...+150	$^{\circ}C$
$T_{VJM}$		150	
$T_{stg}$		-40...+150	
$P_{tot}$	$T_C=25^{\circ}C$	100	W
$V_{ISOL}$	50/60Hz, RMS $I_{ISOL} \leq 1mA$	2500	V~
$M_d$	Mounting torque Terminal connection torque (M4)	1.5/13 1.5/13	Nm/lb.in.
Weight		30	g

# SUR2x30-08, SUR2x30-10

## Ultra Fast Recovery Epitaxial Diodes

Symbol	Test Conditions	Characteristic Values		Unit
		typ.	max.	
<b>I<sub>R</sub></b>	$T_{VJ}=25^{\circ}\text{C}; V_R=V_{RRM}$		750	uA
	$T_{VJ}=25^{\circ}\text{C}; V_R=0.8 \cdot V_{RRM}$		250	uA
	$T_{VJ}=125^{\circ}\text{C}; V_R=0.8 \cdot V_{RRM}$		7	mA
<b>V<sub>F</sub></b>	$I_F=30\text{A}; T_{VJ}=150^{\circ}\text{C}$		2	V
	$T_{VJ}=25^{\circ}\text{C}$		2.4	
<b>V<sub>TO</sub></b>	For power-loss calculations only		1.5	V
<b>r<sub>T</sub></b>	$T_{VJ}=T_{VJM}$		12.5	mΩ
<b>R<sub>thJC</sub></b> <b>R<sub>thCK</sub></b>		0.05	1.25	K/W
<b>t<sub>rr</sub></b>	$I_F=1\text{A}; -di/dt=100\text{A}/\mu\text{s}; V_R=30\text{V}; T_{VJ}=25^{\circ}\text{C}$	35	50	ns
<b>I<sub>RM</sub></b>	$V_R=540\text{V}; I_F=30\text{A}; -di_F/dt=240\text{A}/\mu\text{s}; L \leq 0.05\mu\text{H}; T_{VJ}=100^{\circ}\text{C}$	16	18	A

### FEATURES

- \* International standard package miniBLOC (ISOTOP compatible)
- \* Isolation voltage 2500 V~
- \* 2 independent FRED in 1 package
- \* Planar passivated chips
- \* Very short recovery time
- \* Extremely low switching losses
- \* Low I<sub>RM</sub>-values
- \* Soft recovery behaviour

### APPLICATIONS

- \* Antiparallel diode for high frequency switching devices
- \* Antisaturation diode
- \* Snubber diode
- \* Free wheeling diode in converters and motor control circuits
- \* Rectifiers in switch mode power supplies (SMPS)
- \* Inductive heating and melting
- \* Uninterruptible power supplies (UPS)
- \* Ultrasonic cleaners and welders

### ADVANTAGES

- \* High reliability circuit operation
- \* Low voltage peaks for reduced protection circuits
- \* Low noise switching
- \* Low losses
- \* Operating at lower temperature or space saving by reduced cooling

# SUR2x30-08, SUR2x30-10

## Ultra Fast Recovery Epitaxial Diodes

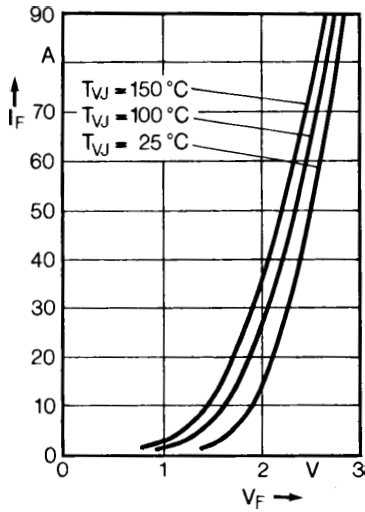


Fig. 1 Forward current versus voltage drop.

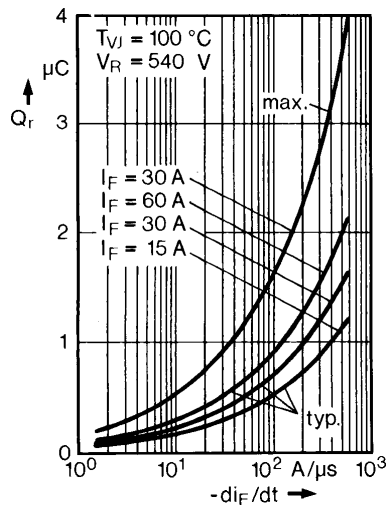


Fig. 2 Recovery charge versus  $-di_F/dt$ .

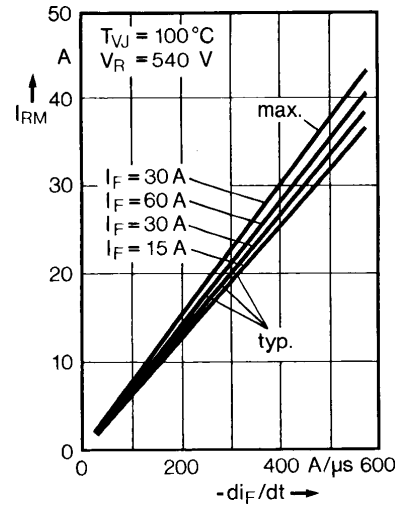


Fig. 3 Peak reverse current versus  $-di_F/dt$ .

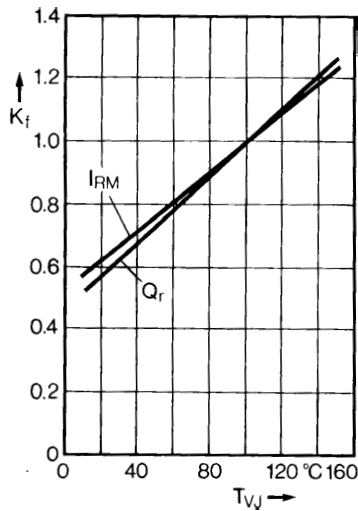


Fig. 4 Dynamic parameters versus junction temperature.

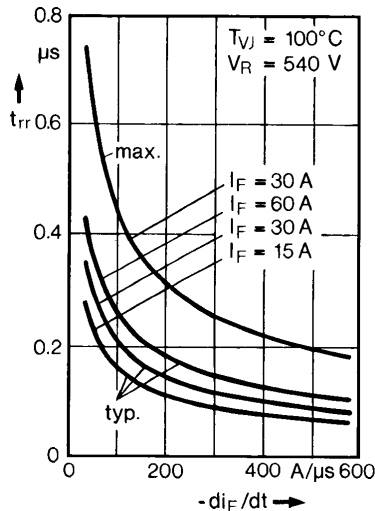


Fig. 5 Recovery time versus  $-di_F/dt$ .

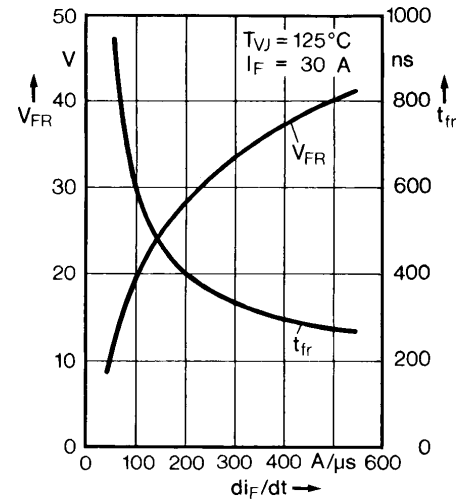


Fig. 6 Peak forward voltage versus  $di_F/dt$ .

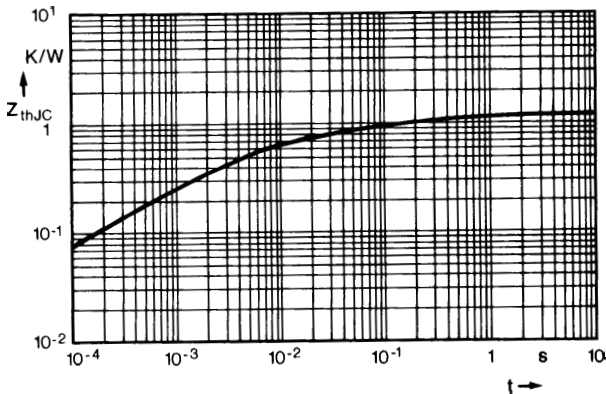


Fig. 7 Transient thermal impedance junction to case.